



N-Channel Enhancement-Mode Vertical DMOS FET

Features

- ▶ Low threshold
- ▶ High input impedance
- ▶ Low input capacitance (110pF max.)
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage

Applications

- ▶ Logic level interfaces - ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Battery operated systems
- ▶ Photo voltaic drives
- ▶ Analog switches
- ▶ General purpose line drivers
- ▶ Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Option	BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)	$I_{D(ON)}$ (min) (mA)	$V_{GS(TH)}$ (max) (V)
	TO-243AA (SOT-89)				
TN2501	TN2501N8-G	18	2.5	250	1.0

-G indicates package is RoHS compliant ('Green')



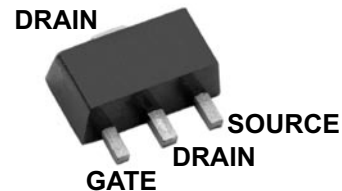
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	$\pm 15V$
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* Distance of 1.6mm from case for 10 seconds.

Pin Configuration



TO-243AA (SOT-89) (N8)

Product Marking

TN5UW W = Code for week sealed
 _____ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-243AA (SOT-89) (N8)

Thermal Characteristics

Package	I _D (continuous) [†] (mA)	I _D (pulsed) (mA)	Power Dissipation @T _A = 25°C (W)	θ _{jc} (°C/W)	θ _{ja} (°C/W)	I _{DR} [†] (mA)	I _{DRM} (mA)
TO-243AA (SOT-89)	400	560	1.6‡	15	78‡	560	750

Notes:

- † I_D (continuous) is limited by max rated T_J.
- ‡ Mounted on FR5 Board, 25mm x 25mm x 1.57mm.

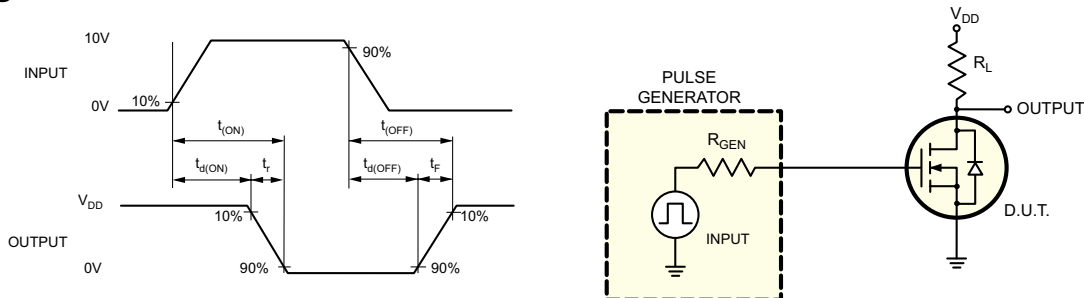
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV _{DSS}	Drain-to-source breakdown voltage	18	-	-	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate threshold voltage	0.3	-	1.0	V	V _{GS} = V _{DS} , I _D = 1.0mA
ΔV _{GS(th)}	Change in V _{GS(th)} with temperature	-	-	-4.0	mV/°C	V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate body leakage	-	-	100	nA	V _{GS} = ±15V, V _{DS} = 0V
I _{DSS}	Zero gate voltage drain current	-	-	10	μA	V _{GS} = 0V, V _{DS} = Max Rating
		-	-	1.0	mA	V _{DS} = 0.8Max Rating, V _{GS} = 0V, T _A = 125°C
I _{D(ON)}	On-state drain current	250	600	-	A	V _{GS} = V _{DS} = 3.0V
R _{DS(ON)}	Static drain-to-source on-state resistance	-	-	25	Ω	V _{GS} = 1.2V, I _D = 3.0mA
		-	-	3.5		V _{GS} = 2.0V, I _D = 50mA
		-	-	2.5		V _{GS} = 3.0V, I _D = 200mA
ΔR _{DS(ON)}	Change in R _{DS(ON)} with temperature	-	-	0.75	%/°C	V _{GS} = 3.0V, I _D = 200mA
G _{FS}	Forward transductance	150	300	-	mmho	V _{DS} = 3.0V, I _D = 200mA
C _{ISS}	Input capacitance	-	-	110	pF	V _{GS} = 0V, V _{DS} = 15V, f = 1.0MHz
C _{OSS}	Common source output capacitance	-	-	60		
C _{RSS}	Reverse transfer capacitance	-	-	35		
t _{d(ON)}	Turn-on delay time	-	-	5.0	ns	V _{DD} = 15V, I _D = 250mA, R _{GEN} = 25Ω
t _r	Rise time	-	-	15		
t _{d(OFF)}	Turn-off delay time	-	-	15		
t _f	Fall time	-	-	8.0		
V _{SD}	Diode forward voltage drop	-	1.1	1.8	V	V _{GS} = 0V, I _{SD} = 200mA
t _{rr}	Reverse recovery time	-	100	-	ns	V _{GS} = 0V, I _{SD} = 200mA

Notes:

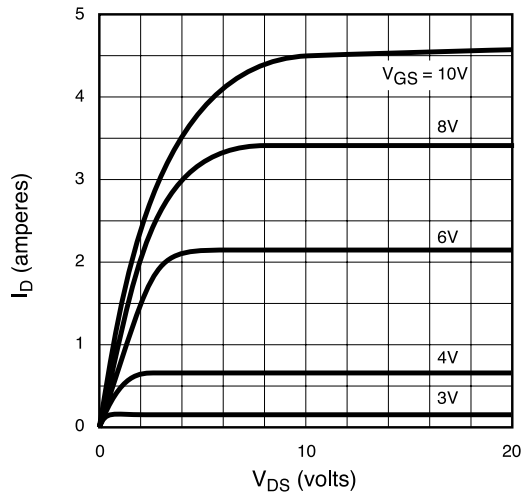
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300μs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

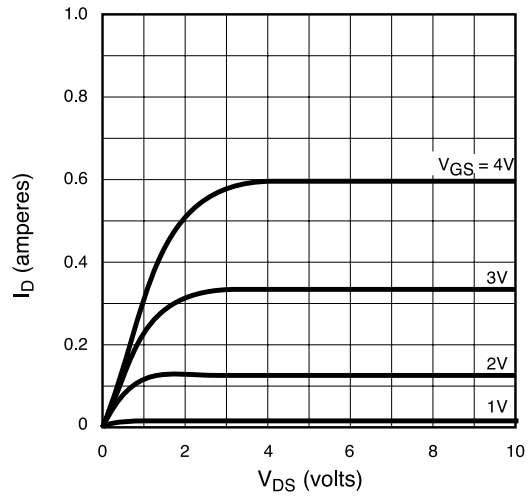


Typical Performance Curves

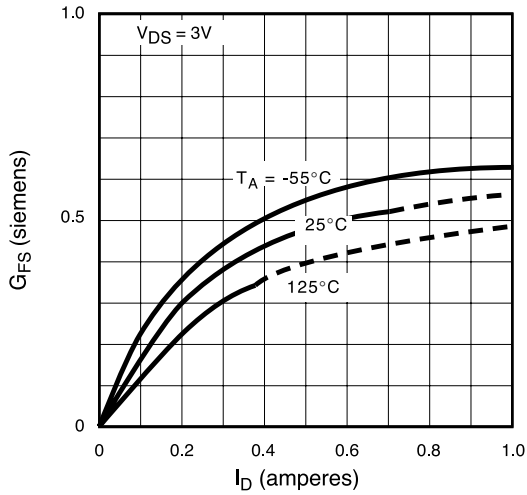
Output Characteristics



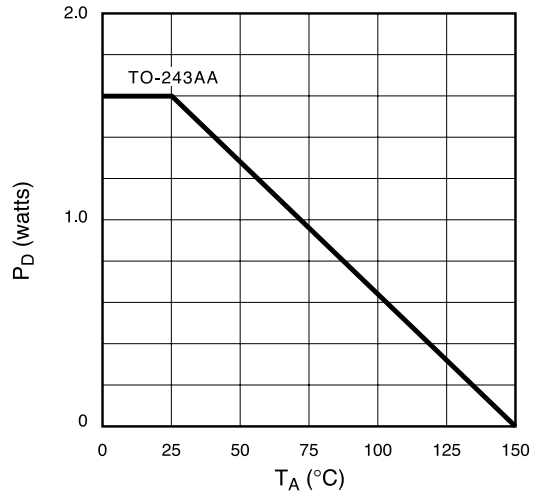
Saturation Characteristics



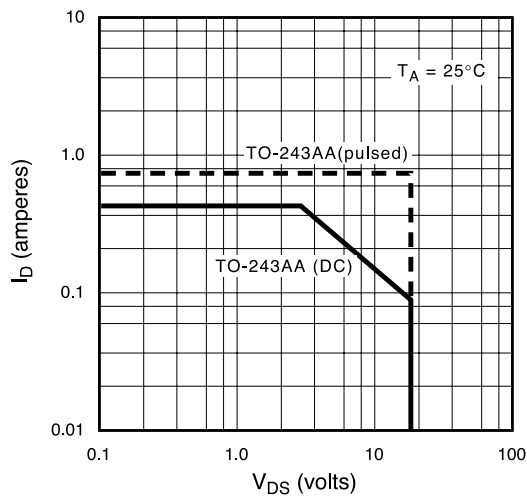
Transconductance vs. Drain Current



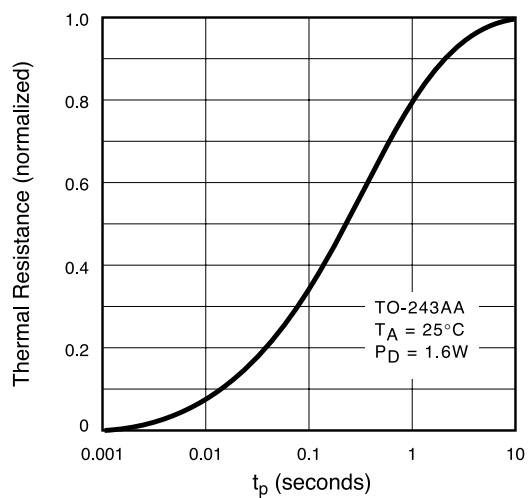
Power Dissipation vs. Ambient Temperature



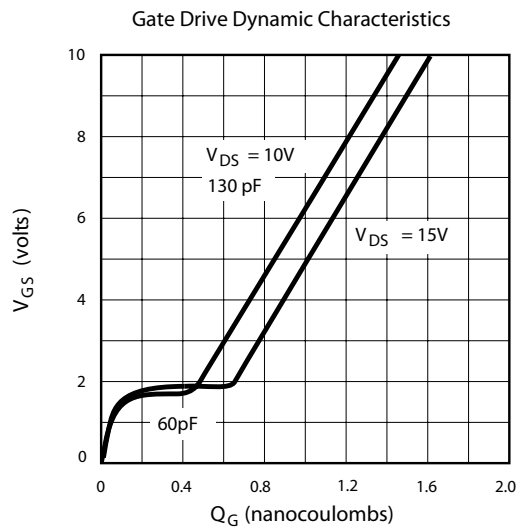
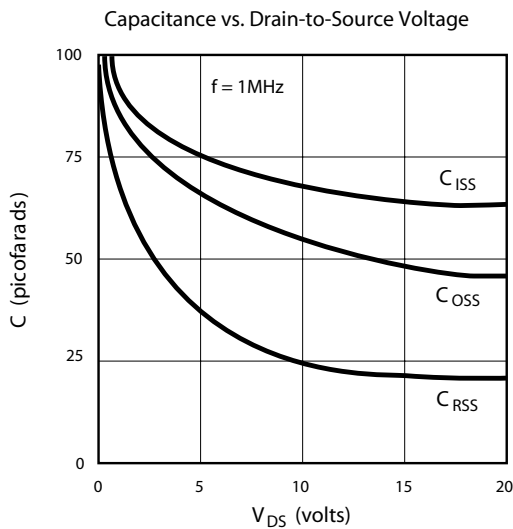
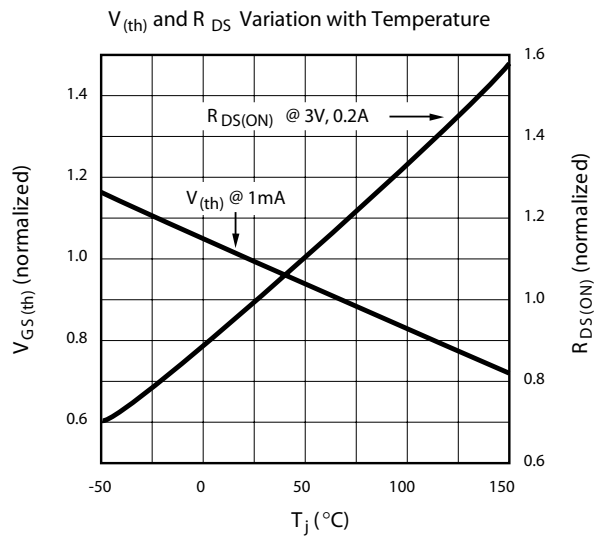
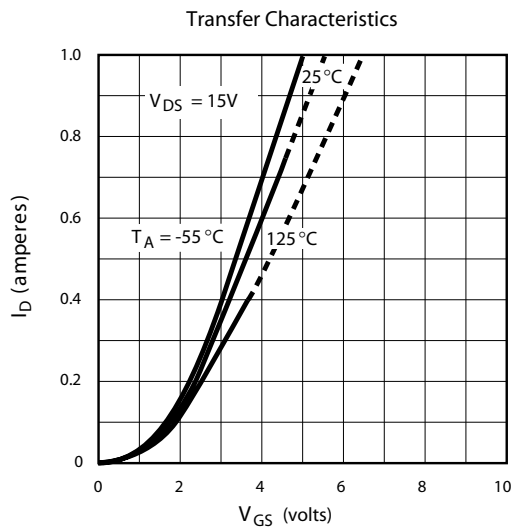
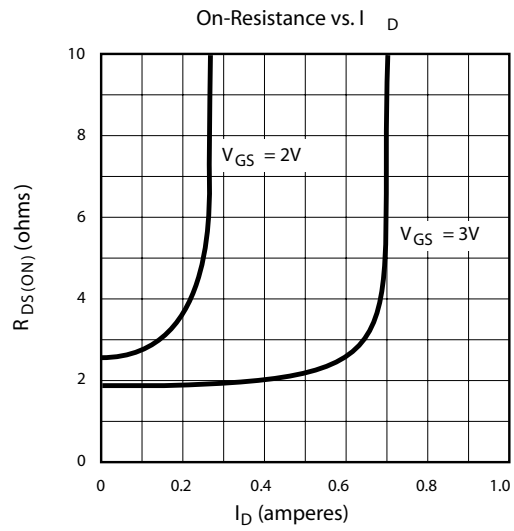
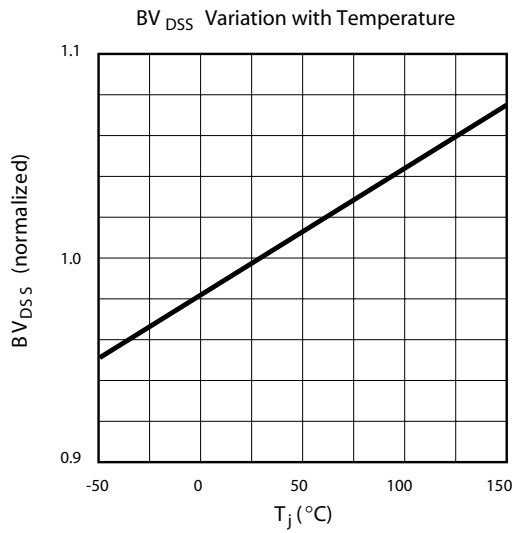
Maximum Rated Safe Operating Area



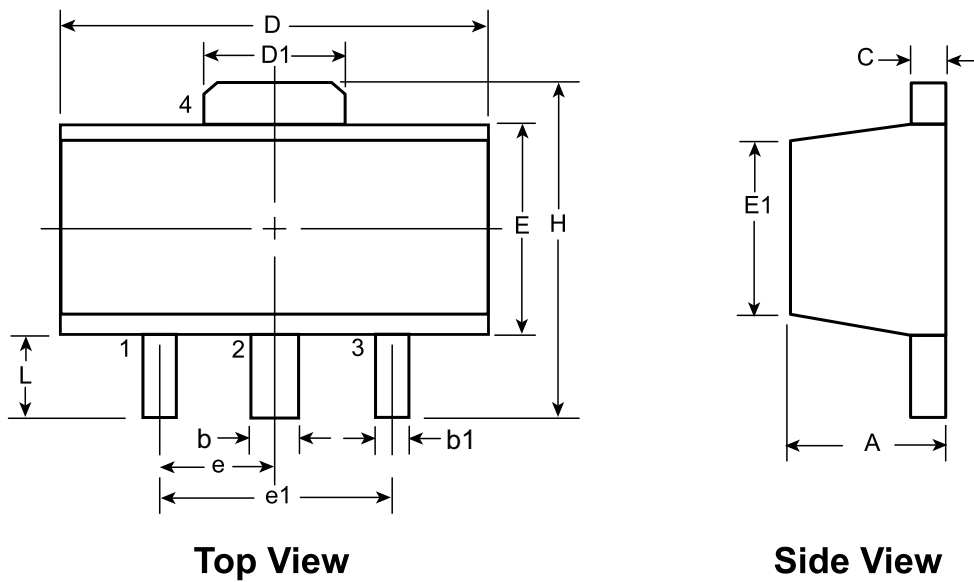
Thermal Response Characteristics



Typical Performance Curves (cont.)



3-Lead TO-243AA (SOT-89) Package Outline (N8)



Top View

Side View

Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L	
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.13	1.50 BSC	3.00 BSC	3.94	0.89	
	NOM	-	-	-	-	-	-	-	-			-	-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20	

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version D070908.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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